

垂直磁気異方性を有する SmFe_2 に作用するスピン軌道トルクの検出

Detection of spin-orbit torque on magnetostrictive SmFe_2 thin films with perpendicular magnetic anisotropy for piezoelectronic magnetic tunnel junctions

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We have proposed stress-assist magnetization reversal (SAMR) for ultra-low power consumption nonvolatile memories[1]. To realize magnetic memories using SAMR, an understanding of spin injection to a SAMR material is strongly required. However, there is no report on spin injection to a SAMR material despite their novel functionalities. In this study, we detected pure spin current injection to a kind of SAMR material, SmFe_2 , by measuring second harmonic method[2].

A SmFe_2 thin film was sputtered on a Ta-buffered Si/SiO₂ substrate at 200°C and capped with a Ta layer. Subsequently annealing was performed at 450°C in a vacuum for 1 hour. The multilayer was patterned into a Hall bar shape with $200 \times 1000 \mu\text{m}^2$ by photolithography and ion-milling, as shown in Fig.1.

Figure 2 shows second harmonic Hall resistances as a function of the azimuth angle ϕ_H of an external magnetic field, where applied current density was $4.2 \times 10^5 \text{ A/cm}^2$, and the magnetic field strength was set to 1.8 and 9.4 kOe. $R_{xy}^{2\omega} - \phi_H$ curves were reproduced by $\cos\phi_H$, which is originated from the damping-like spin-orbit torque (SOT) and anomalous Nernst effect. The amplitude of the $\cos\phi_H$ component also depended on the magnetic field strength, which implies the existence of the SOT contribution.

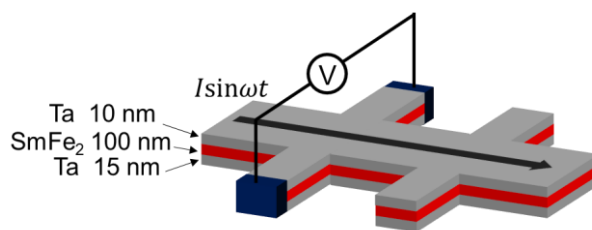


Fig. 1 Structure of a sample

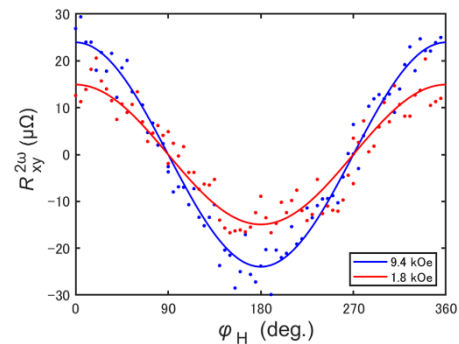


Fig. 2 Second harmonic Hall resistances measured at 1.8 and 9.4 kOe

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Refs: [1] N. Saito, M. Yamada, S. Nakagawa, J. Appl. Phys. **103**, 07A706 (2008). [2] C. O. Avci, *et al.* Phys. Rev. B **90**, 224427 (2014).